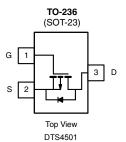


# P-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	- 40				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.083				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.110				
I <sub>D</sub> (A)	- 3.6				
Configuration	Single				

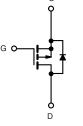


#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- AEC-Q101 Qualified<sup>c</sup>
- 100 % R<sub>q</sub> and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



ROHS COMPLIANT HALOGEN FREE



P-Channel	MOSFET

ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and Halogen-free	DTS4501

ABSOLUTE MAXIMUM RATINGS	<b>S</b> (T <sub>C</sub> = 25 °C, unles	s otherwise noted	d)	
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	$V_{DS}$	- 40	V	
Gate-Source Voltage	$V_{GS}$	± 20	V	
Continuous Drain Current	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	- 3.6	
	T <sub>C</sub> = 125 °C		- 2.6	
Continuous Source Current (Diode Conduction	Is	- 3.6	Α	
Pulsed Drain Current <sup>a</sup>	I <sub>DM</sub>	- 18		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	- 12	
Single Pulse Avalanche Energy	L = 0.1 MH	E <sub>AS</sub>	7.2	mJ
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C		3	10/
	T <sub>C</sub> = 125 °C	$P_{D}$	1	W
Operating Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>b</sup>	$R_{thJA}$	166	°C/W	
Junction-to-Foot (Drain)		R <sub>thJF</sub>	50		

### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. When mounted on 1" square PCB (FR-4 material).
- c. Parametric verification ongoing.



PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static	1				·	ı	<u> </u>	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = - 250 μA		- 40	-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$		- 2.0	- 2.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 40 V	-	-	- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 40 V, T <sub>J</sub> = 125 °C	-	-	- 50	μΑ	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 40 V, T <sub>J</sub> = 175 °C	-	-	- 150		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} \le -5 V$	- 10	-	-	Α	
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 3 A	-	0.071	0.083		
Drain-Source On-State Resistance <sup>a</sup>		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 3 A, T <sub>J</sub> = 125 °C	-	-	0.116	Ω	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 3 A, T <sub>J</sub> = 175 °C	-	-	0.139		
		V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 2.4 A	-	0.100	0.110		
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub> = - 5 V, I <sub>D</sub> = - 3 A		-	8	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>			-	493	620	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = - 25 V, f = 1 MHz	-	76	95		
Reverse Transfer Capacitance	C <sub>rss</sub>			-	51	65		
Total Gate Charge <sup>c</sup>	Qg			-	10.5	16	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} = -20 \text{ V}, I_{D} = -3 \text{ A}$	-	1.8	-		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			-	2.6	-		
Gate Resistance	R <sub>g</sub>	f = 1 MHz		5	10	15	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	5	8		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = - 20 V, $R_L$ = 6.7 $\Omega$ $I_D$ $\cong$ - 3 A, $V_{GEN}$ = - 10 V, $R_g$ = 1 $\Omega$		-	11	17	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	19	29		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	8	12		
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	- 18	Α	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = - 1.5 A, V <sub>GS</sub> = 0		-	- 0.8	- 1.2	V	

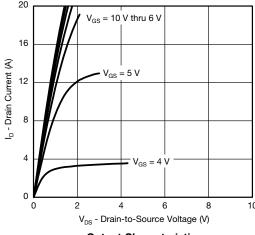
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

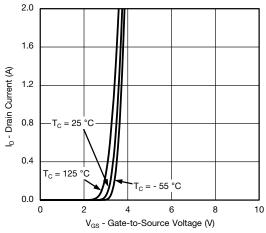
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### **TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)

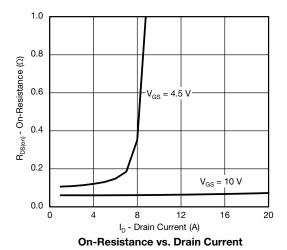
# www.din-tek.jp



#### **Output Characteristics**

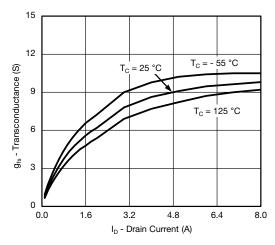


Transfer Characteristics

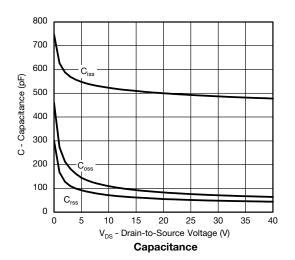


20
16
(4)
12
4
T<sub>C</sub> = 125 °C
T<sub>C</sub> = - 55 °C
V<sub>GS</sub> - Gate-to-Source Voltage (V)

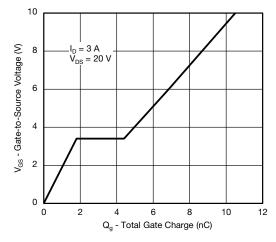
**Transfer Characteristics** 



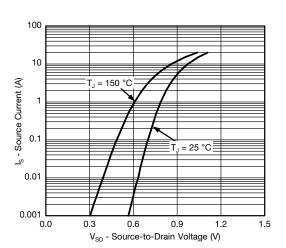
Transconductance



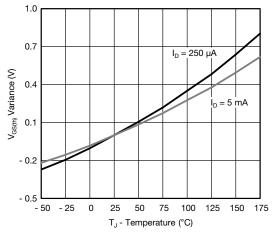
### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \, ^{\circ}\text{C}$ , unless otherwise noted)



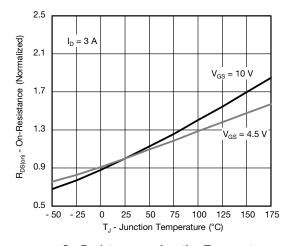
**Gate Charge** 



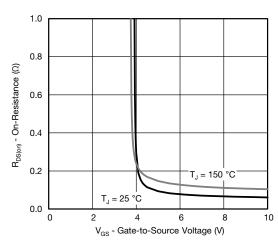
**Source Drain Diode Forward Voltage** 



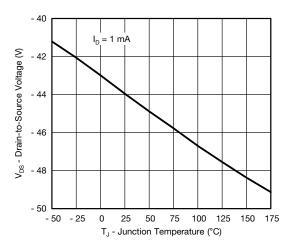
**Threshold Voltage** 



On-Resistance vs. Junction Temperature



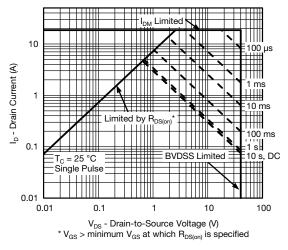
On-Resistance vs. Gate-to-Source Voltage



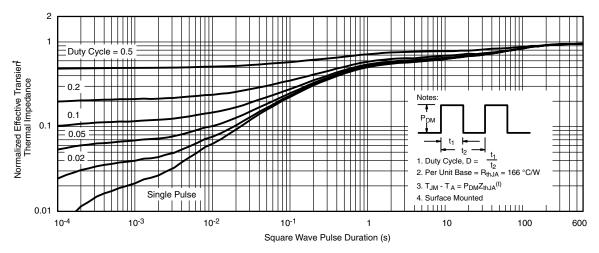
**Drain Source Breakdown vs. Junction Temperature** 



# **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



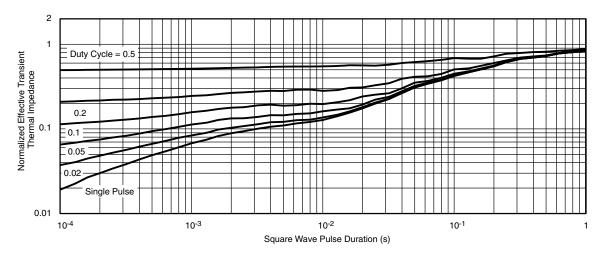
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



**THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

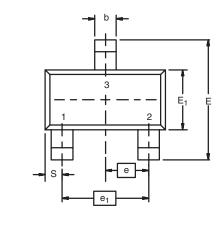
#### Note

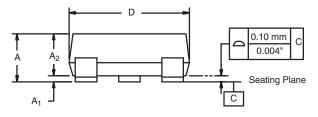
- · The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single

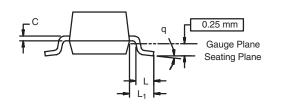
pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



# SOT-23 (TO-236): 3-LEAD





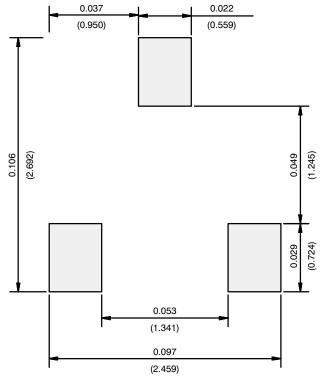


Dim	MILLIM	IETERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A <sub>1</sub>	0.01	0.10	0.0004	0.004	
A <sub>2</sub>	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E <sub>1</sub>	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e <sub>1</sub>	1.90	1.90 BSC		8 Ref	
L	0.40	0.60	0.016	0.024	
L <sub>1</sub>	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
ECN: S-03946-Rev. K. 09-	Jul-01	•	<u> </u>		

DWG: 5479



### **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index





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